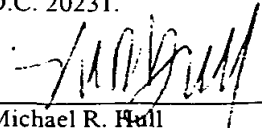




PATENT
29926/37833

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Hyung-Bok Choi)	I hereby certify that this paper and the
)	documents referred to as enclosed
Serial No.: 10/054,528)	therewith are being deposited with the
)	United States Postal Service as first class
Filed: January 22, 2002)	mail, postage prepaid, on March 24,
)	2003, in an envelope addressed to
For: Semiconductor Device and)	Commissioner for Patents, Washington,
Method of Fabricating the Same)	D.C. 20231.
)	
Group Art Unit: 2814)	
)	Michael R. Hall
Examiner: Douglas A. Wille)	Reg. No. 35,902
)	Attorney for Applicant
)	

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the final office action mailed on December 11, 2002, please amend the above-identified patent application, as follows:

In the Specification:

Please replace the paragraph beginning on page 9, line 1, with the following rewritten paragraph:

--Then the upper surface of the seed layer 46 is flattened by carrying out a CMP or an etch-back. That is, the upper surface seed layer 46 is made higher than the upper surface seed separating layer 45 as shown in Fig. 3A, or it may be planarized with the upper surface of the seed separating layer 45 but preferably, the upper surface of the seed layer 46 is disposed above the seed separating layer 45. However, a lower surface of the seed layer 46 is disposed below the upper surface of the seed separating layer 45.--